

Polarized cathode developments and future plans

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Outline

- Major cathode R&D goals for future LCs:
 - To demonstrate full charge productions (highly polarized) for linear colliders, and
 - To develop high performance cathodes.
- Recent measurements on InAlGaAs/AlGaAs:
 - Measurements at SLAC's Cathode Test System (CTS)
 - Measurements at SLAC's Gun Test Lab (GTL)
- Summary for the measurements and future plans

Major parameters of ILC and CLIC e- sources

Parameters	ILC	CLIC
Electrons/microbunch	$\sim 3 \times 10^{10}$	6×10^9
Number of microbunches	2625	312
Width of Microbunch	1 ns	~ 100 ps
Time between microbunches	~ 360 ns	500.2 ps
Width of Macropulse	1 ms	156 ns
Macropulse repetition rate	5 Hz	50 Hz
Charge per macropulse	~ 12600 nC	300 nC
Average current from gun	$63 \mu\text{A}$	$15 \mu\text{A}$
Peak current of microbunch	4.8 A	9.6 A
Current density (1 cm radius)	1.5 A/cm^2	3.0 A/cm^2
Polarization	$>80\%$	$>80\%$

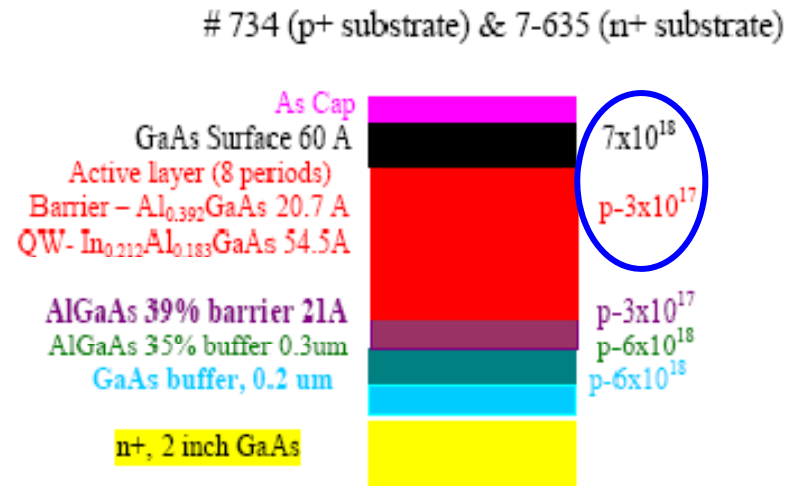
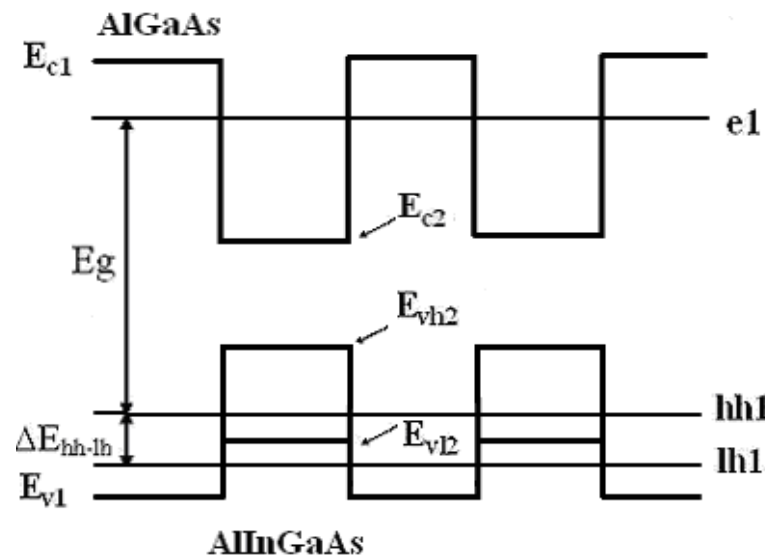


Challenges

- Full charge production limited by space charge and surface charge:
 - Lasers to demonstrate production of polarized electron beam with ILC and CLIC time structures
 - Good polarized cathodes to overcome surface charges with high QE and polarization
 - H.V. gun to overcome space charge, and ultra high vacuum to overcome contamination.
- Cathode candidates for linear colliders:
 - Less charge limit (surface charge and space charge)
 - High polarization (>85%)
 - High QE and QE lifetime

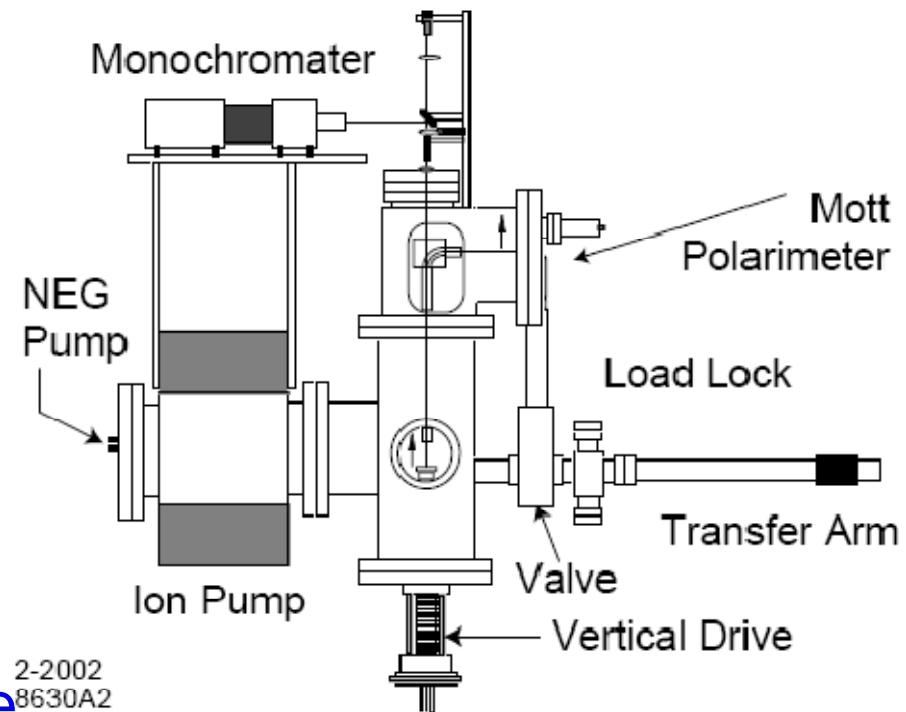
InAlGaAs/AlGaAs

- Strained-well InAlGaAs/AlGaAs structures designed and grown by St. Petersburg in Russia:
 - Large valence band splitting (~ 60 meV) due to combination of deformation and quantum confinement effects in quantum well.
 - Good BBR engineering
 - Thick working layer without strain relaxation
 - $\sim 1\%$ QE and 88%-93% polarization (Russia)



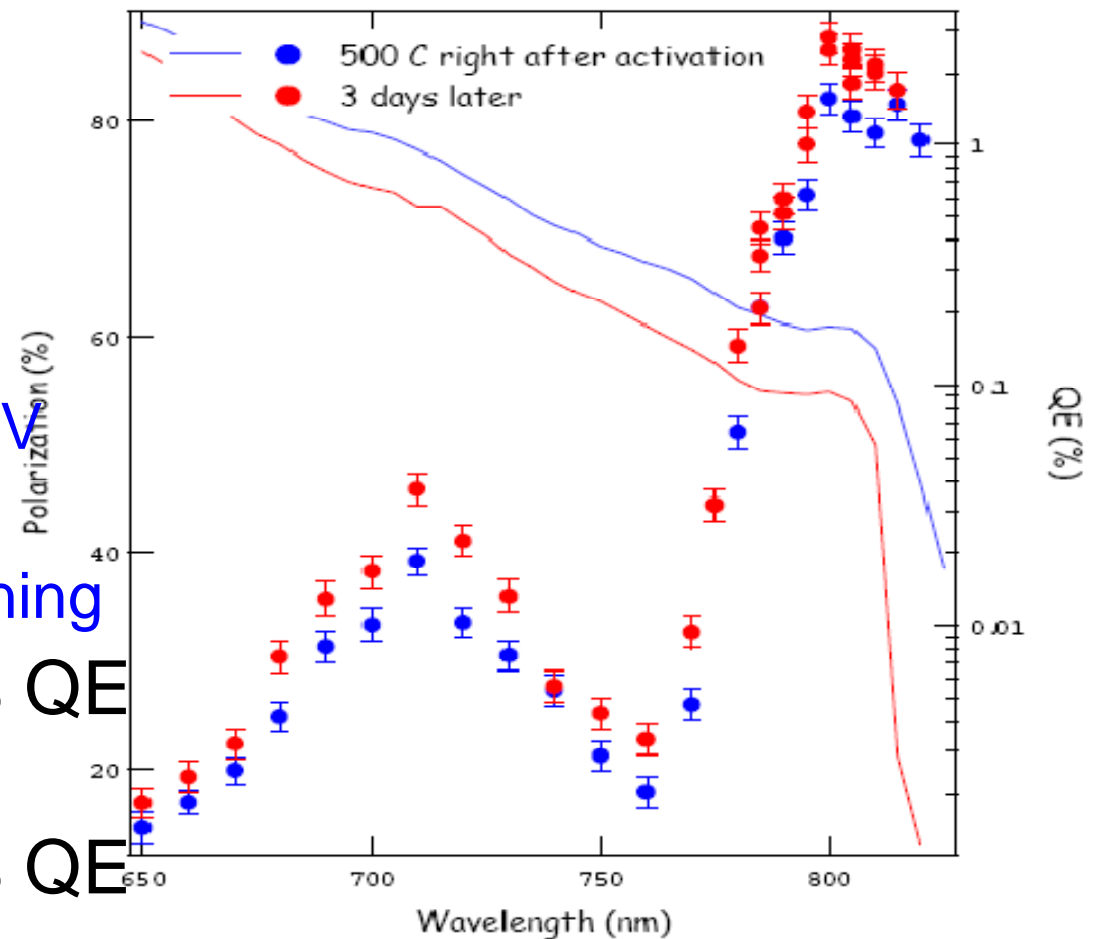
Capabilities at SLAC's Cathode Test System (CTS)

- Cathode preparation and cleaning processes
- QE and polarization measured at 20 KV
- QE and polarization of Cathode can be quickly characterized in few days.
- Drawback: unable to characterize surface charge limit (time evolution of bunch).

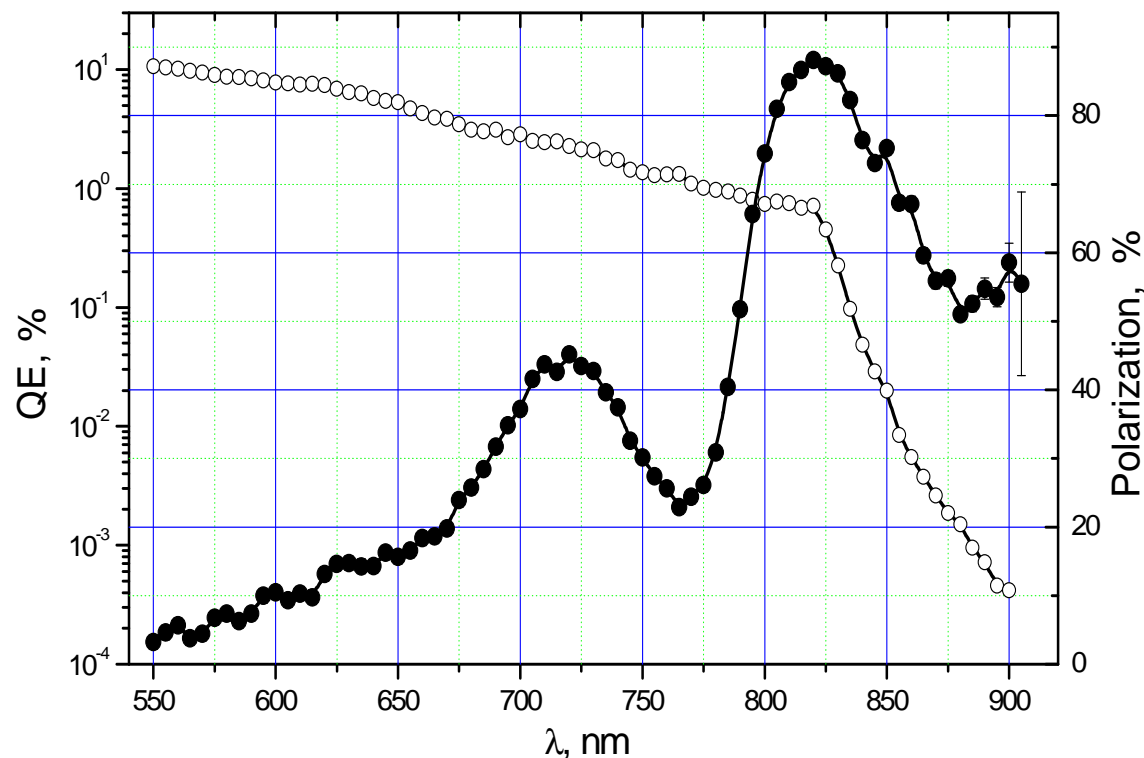


InAlGaAs/AlGaAs @ CTS

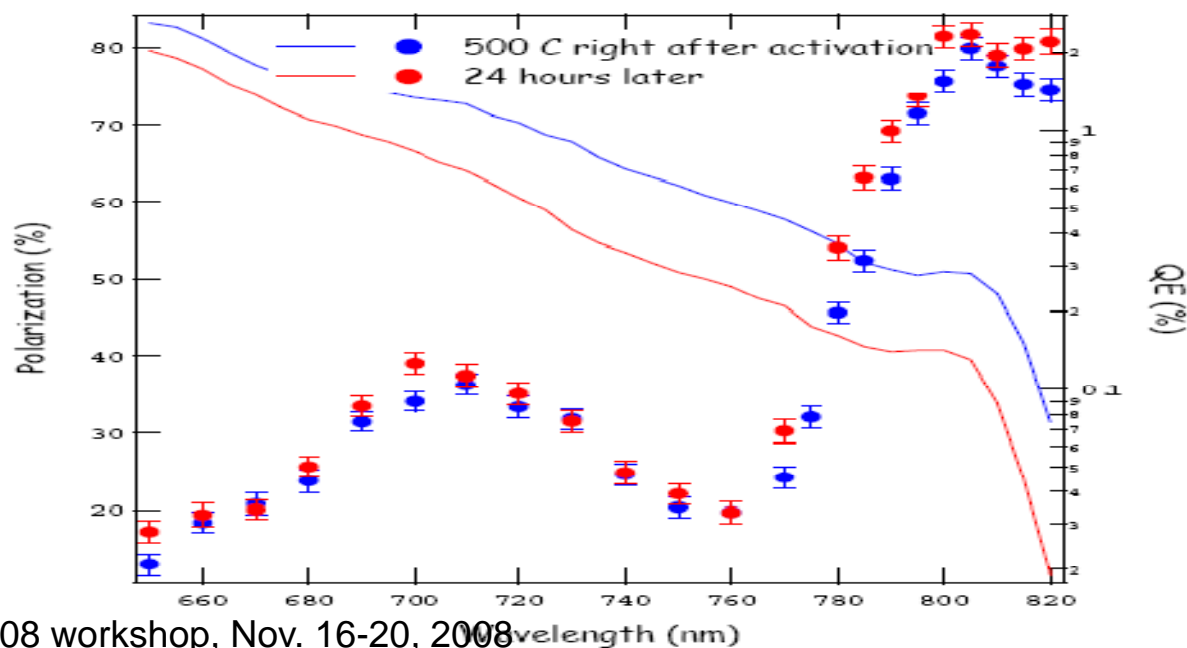
- Polarized cathode measurements:
 - Cathode preparation
 - Chemical cleaning
 - Load lock system to change cathode in UHV
 - Heat cleaning
 - Atomic hydrogen cleaning
- Sample 7-632: ~0.3% QE and 82% polarization.
- Sample 7-635: ~0.2% QE and 87% polarization.



Sample 7-635



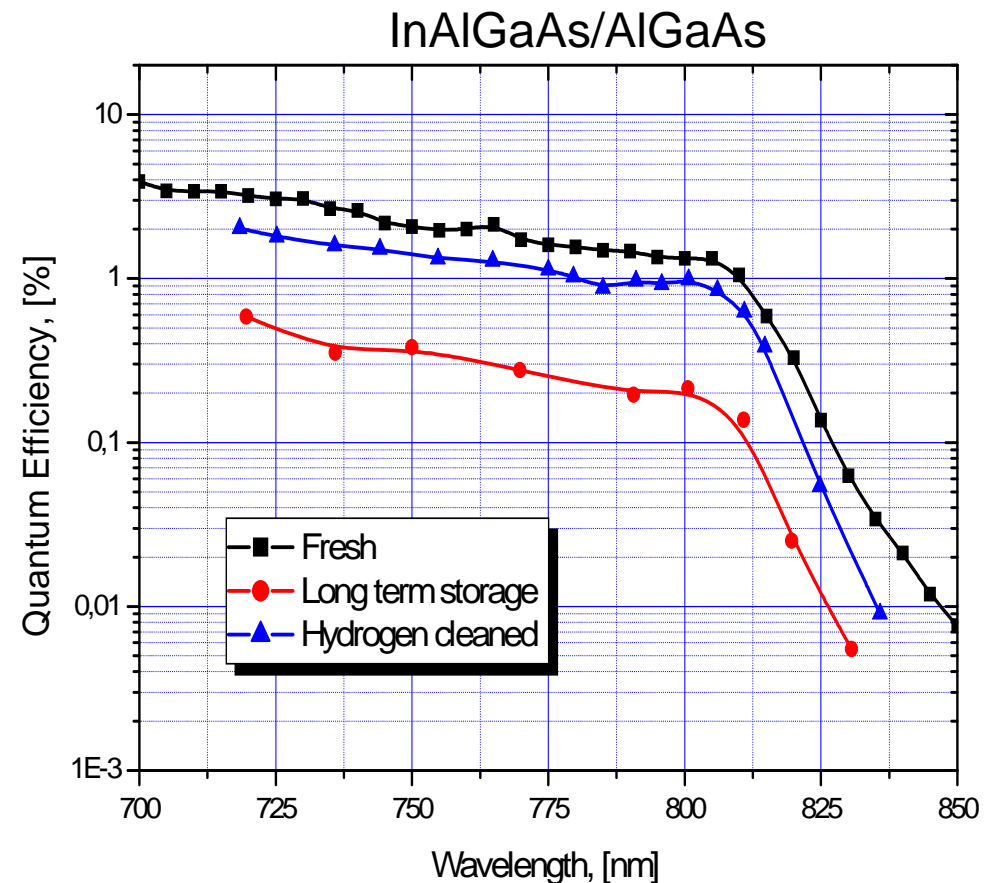
Sample 7-632
 Russian data:
 0.8% QE and
 88% Polarization



Sample 7-632
 CTS/SLAC data:
 0.3% QE and
 82% Polarization

1% of QE recovered by AHC

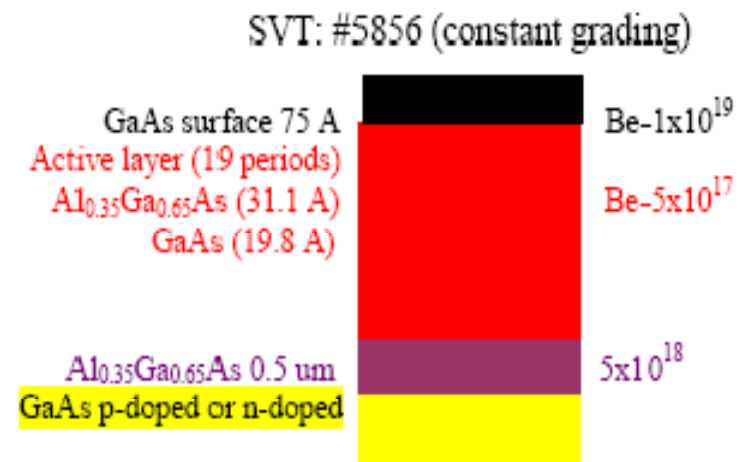
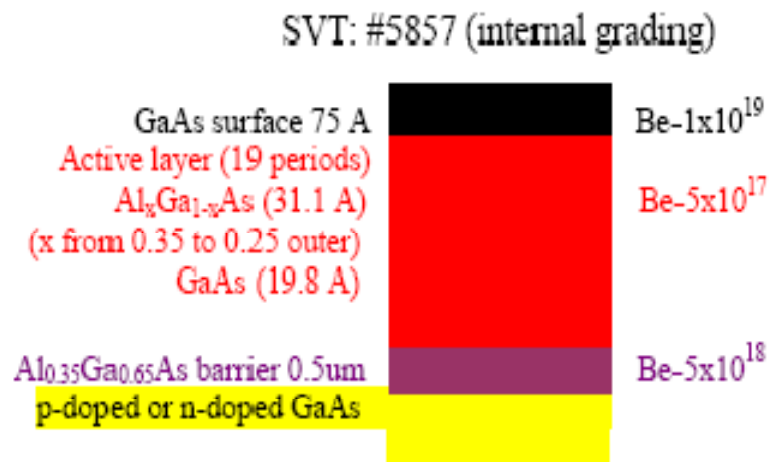
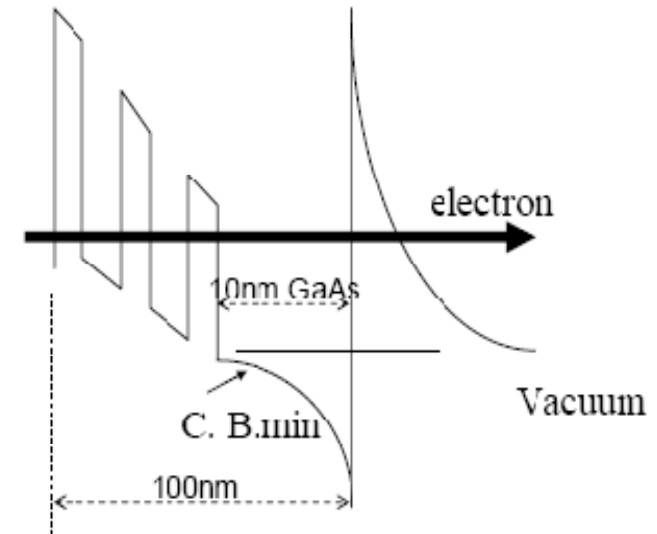
- Probably due to insufficient As-passivation of surface; possible reason: oxide transfer $\text{As} \rightarrow \text{Ga}$ after some time storage.
- Oxides were not removed by conventional heating. But atomic hydrogen cleaning can significantly improve QE for same kind of Russian cathode in Germany.




V. Tioukine, MAMI
(PESP2008)

SBIR graded $\text{Al}_x\text{Ga}_{(1-x)}\text{As}/\text{GaAs}$ (Grown by SVT)

- The graded bandgap active region provides an internal accelerating field for the photo-generated electrons in the conduction band. QE is increased by the field.
- But, the polarization is decreased; need to tune the structure parameters in SBIR phase II.

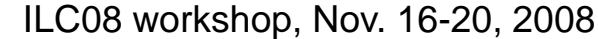




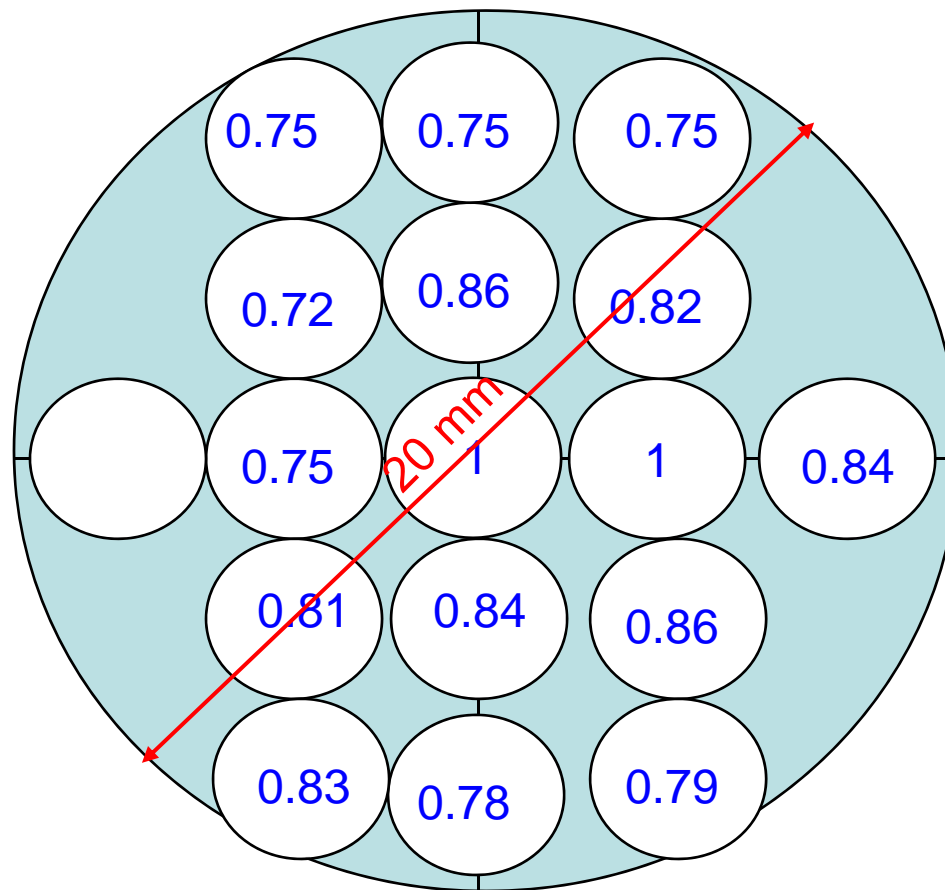
Capabilities at SLAC's Gun Test Lab

- Re-established all measurements at GTL after three-year down time:
 - Surface charge limit (time evolution of bunch)
 - QE and QE lifetime
 - Polarization
- Recent/future activities at SLAC's GTL:
 - Samples of InAlGaAs/AlGaAs (measurements done)
 - Internal graded sample $\text{Al}_x\text{Ga}_{(1-x)}\text{As/GaAs}$
 - To demonstrate full charge production once it is mated to ILC and CLIC lasers
 - Funded R&D programs on new cathodes
- GTL is also available for other R&D projects, such as test different electrodes and guns.

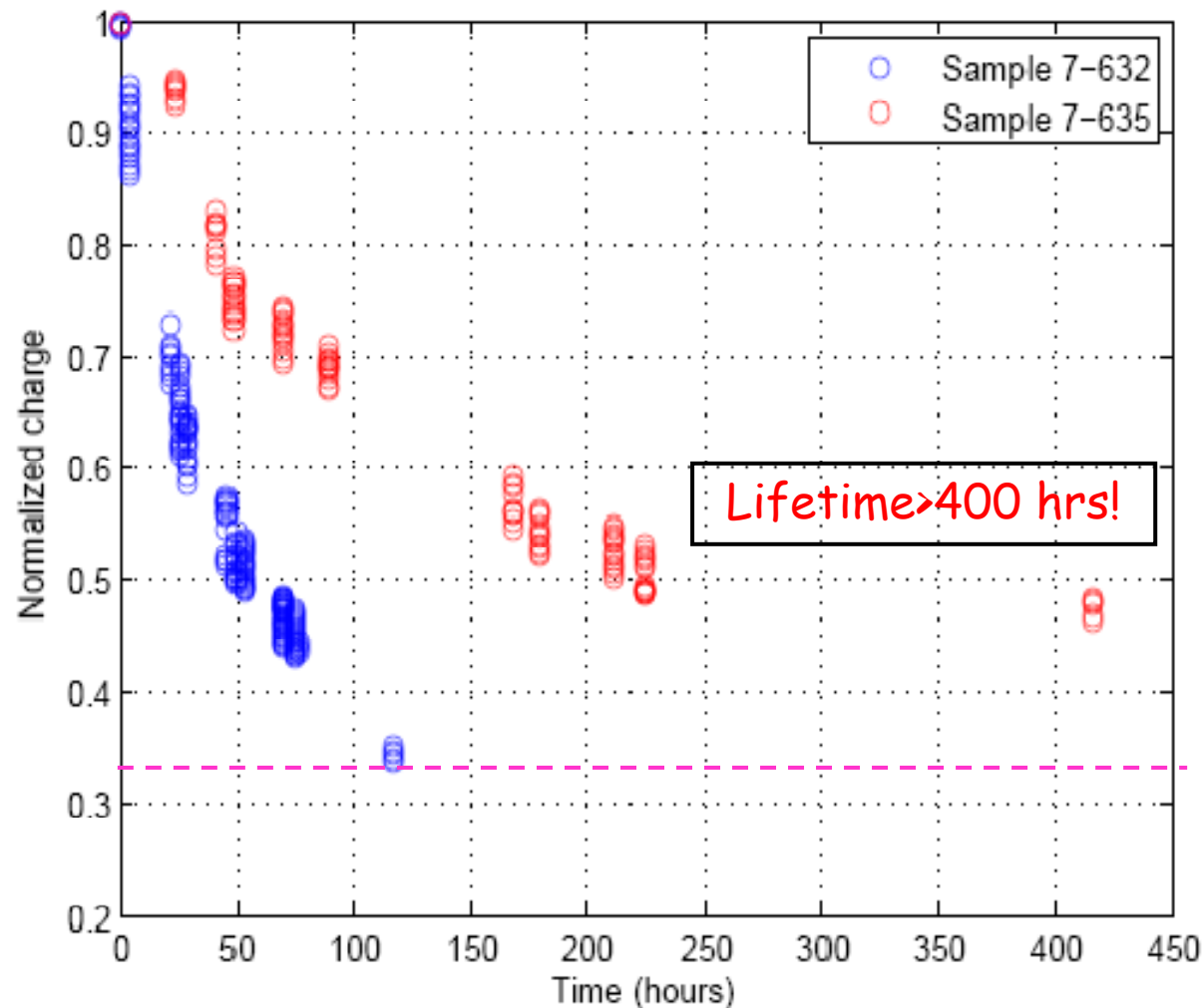
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InAlGaAs/AlGaAs: QE uniformity



InAlGaAs/AlGaAs: QE lifetime

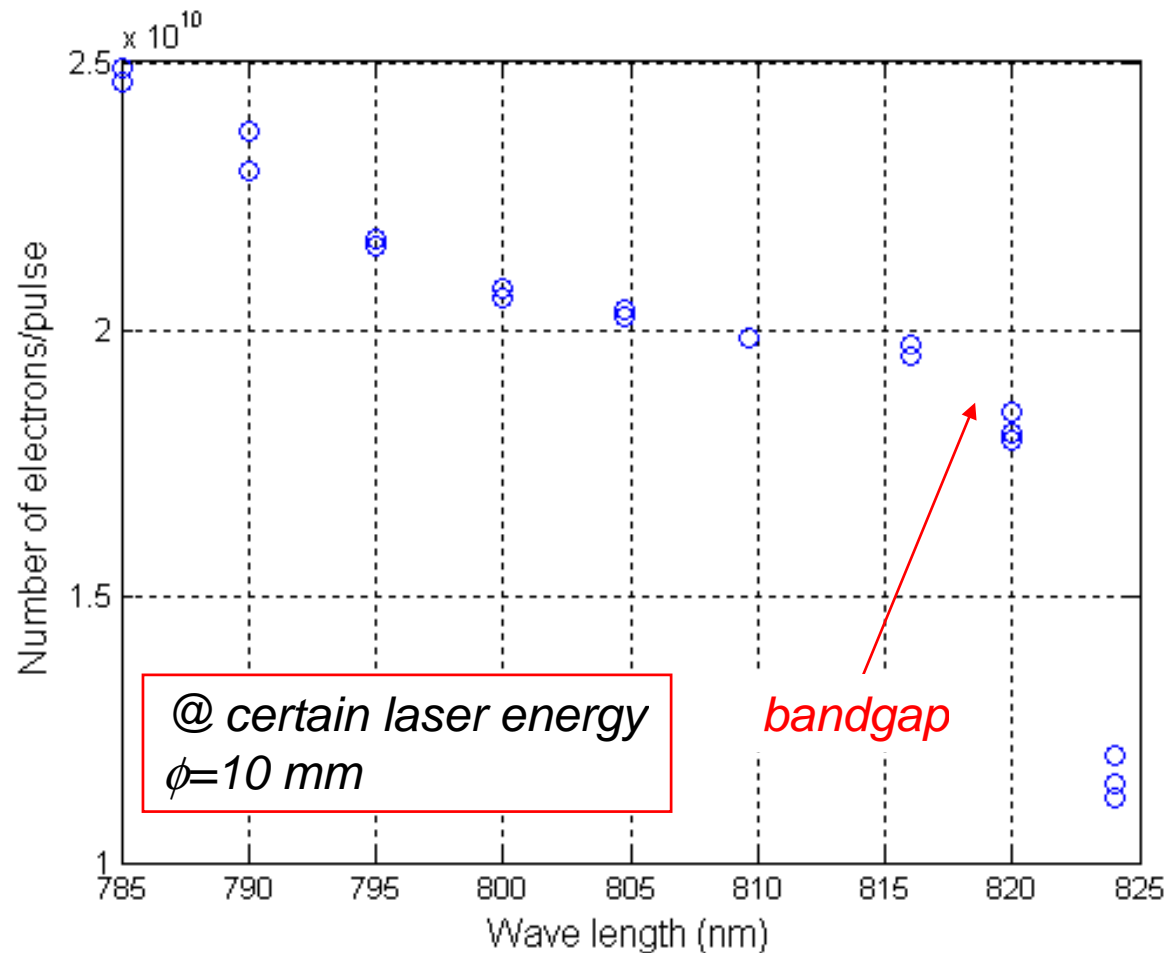


Only difference:

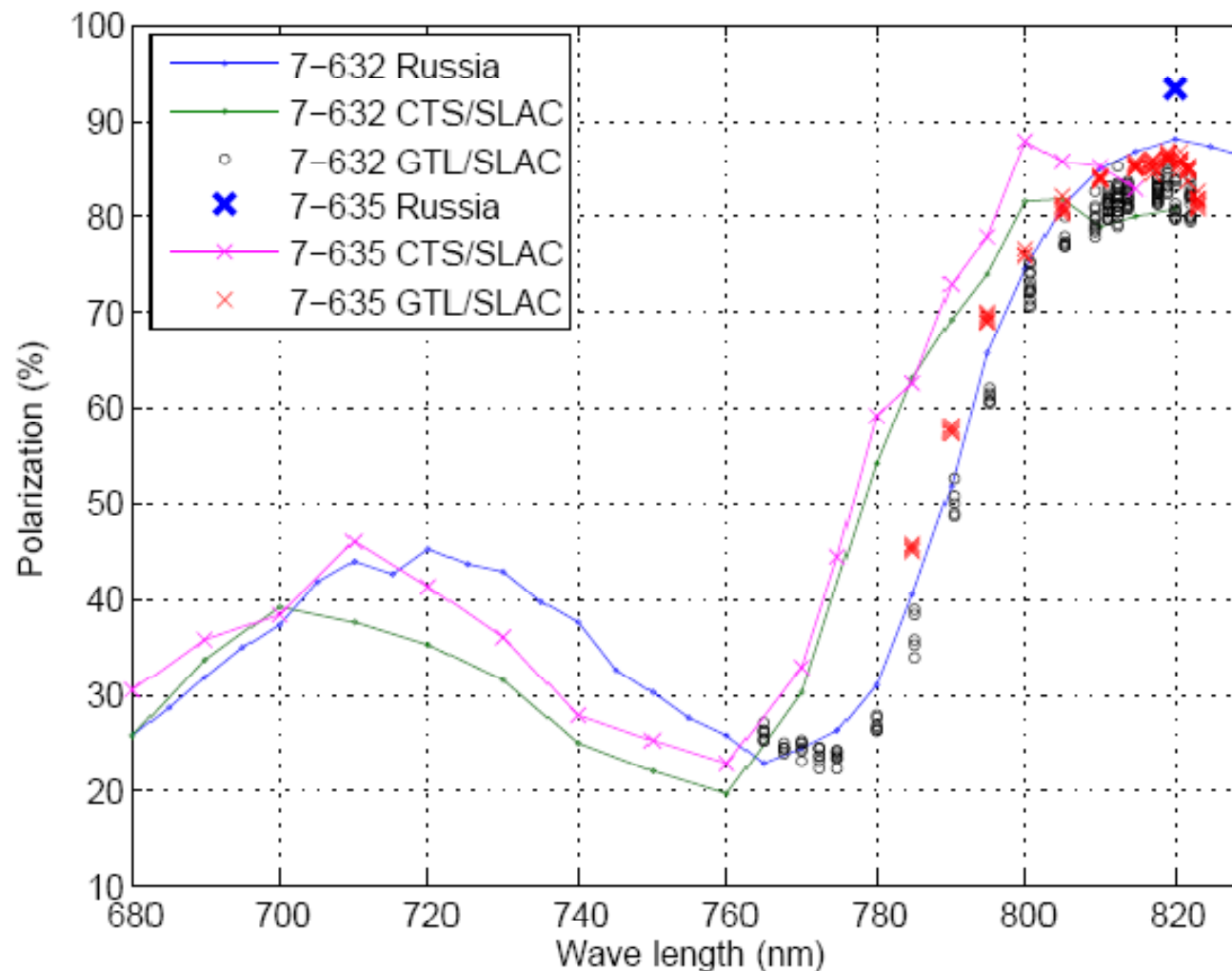
7-632 12 periods
active layers

7-635 8 periods of
active layer

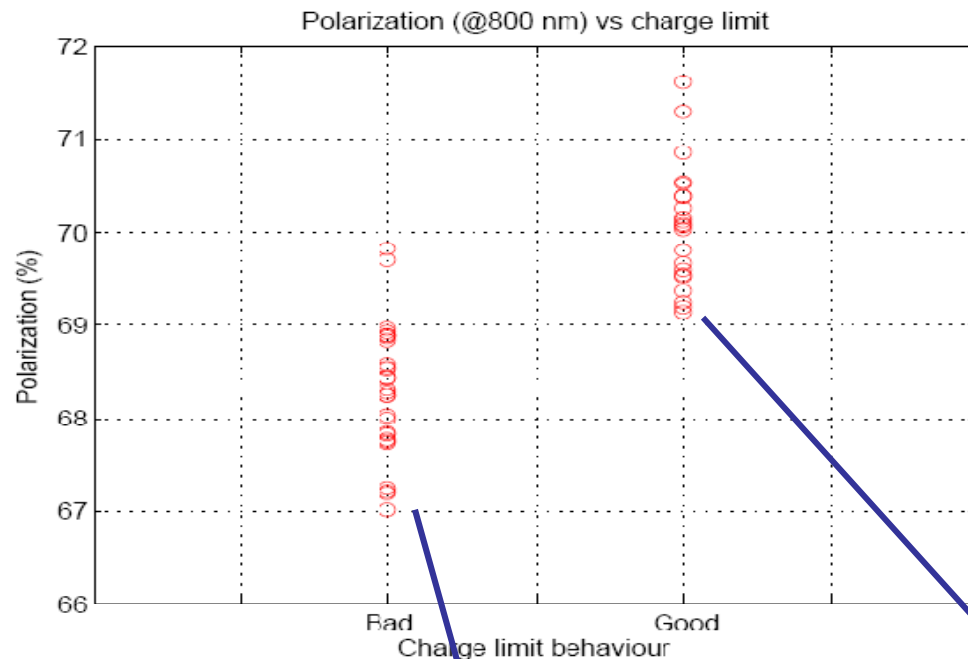
InAlGaAs/AlGaAs: bandgap



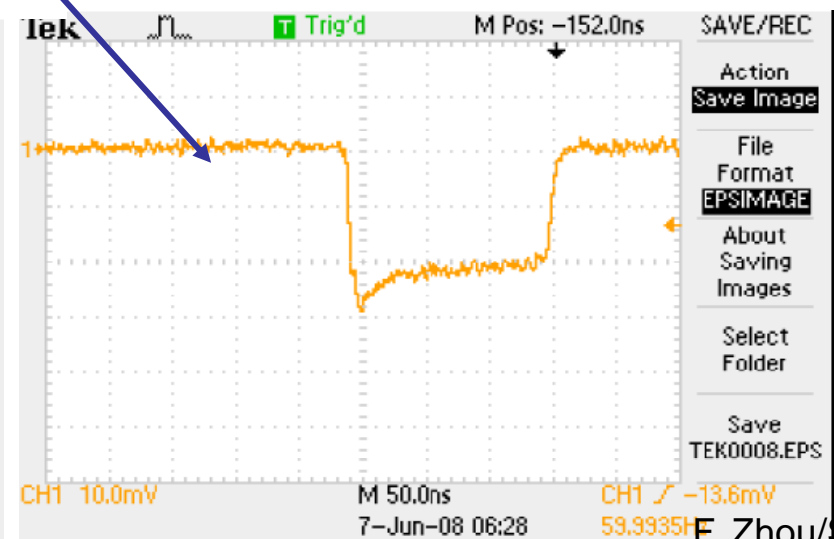
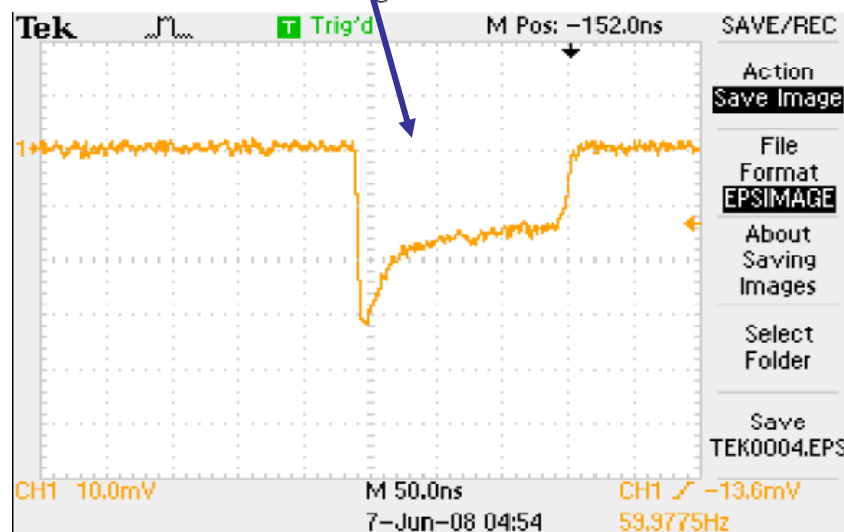
InAlGaAs/AlGaAs: polarization measurements



InAlGaAs/AlGaAs: polarization vs surface charge limit

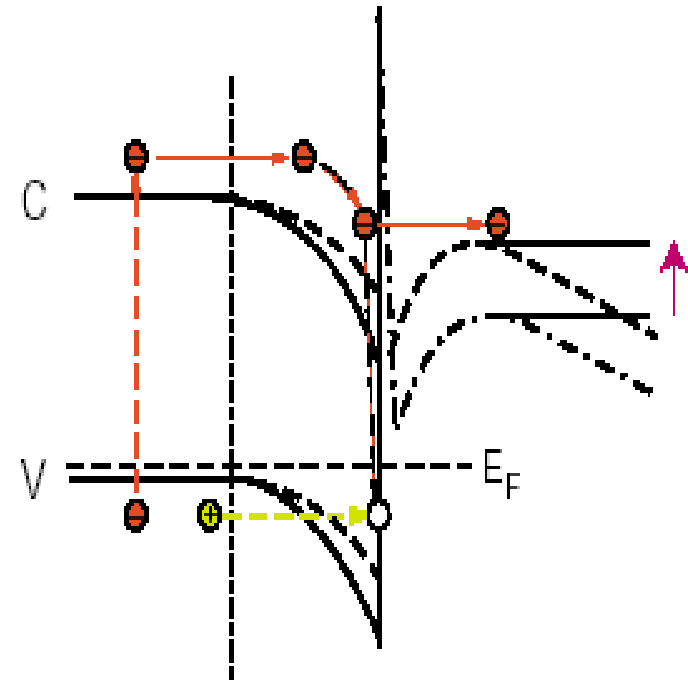


- The cathode is driven into saturation, electrons photoexcited into conduction band can still escape if they diffuse to a non-saturated region.
- But, these electrons spend long time inside structure so it is likely that they suffer spin relaxation.

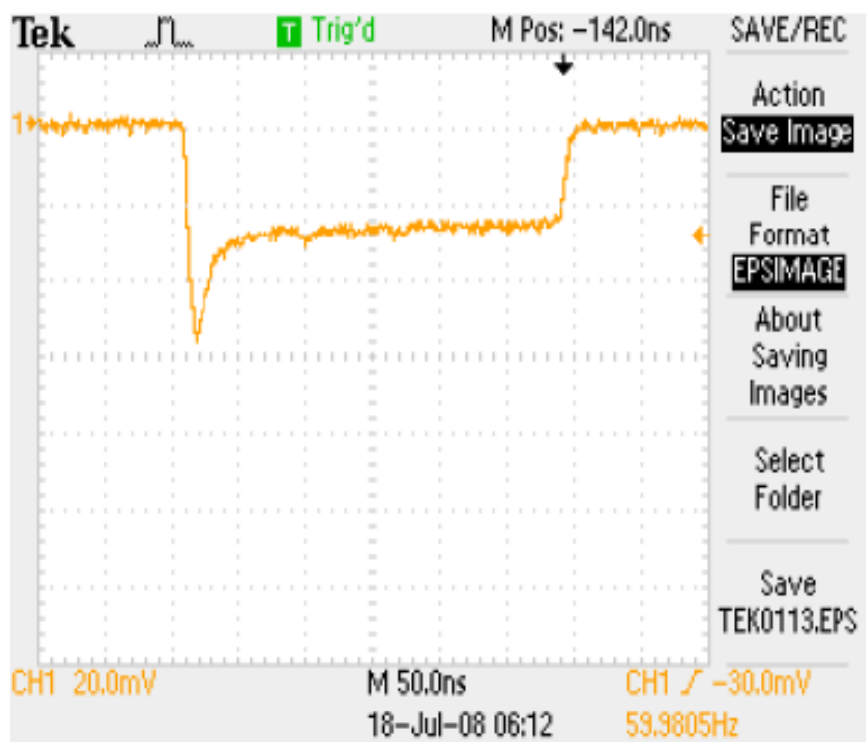


Surface photovoltaic effect - surface charge limit

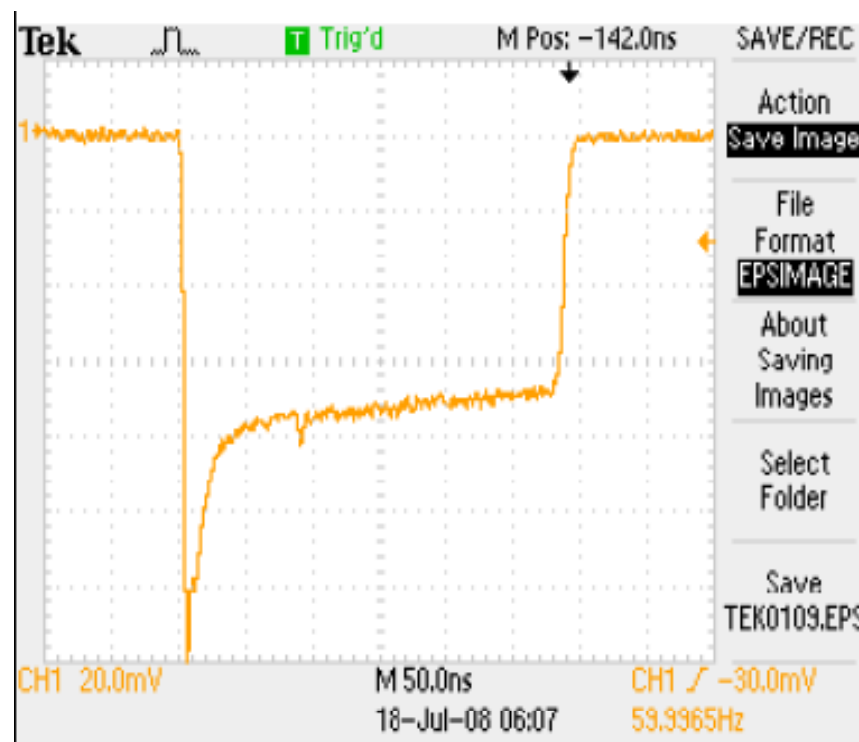
- Photon absorption excites electrons to conduction band
- Electrons can be trapped near the surface
- Electrostatic potential from trapped electrons raised affinity.
- Increased affinity decreases emission probability.



Surface charge: laser energy

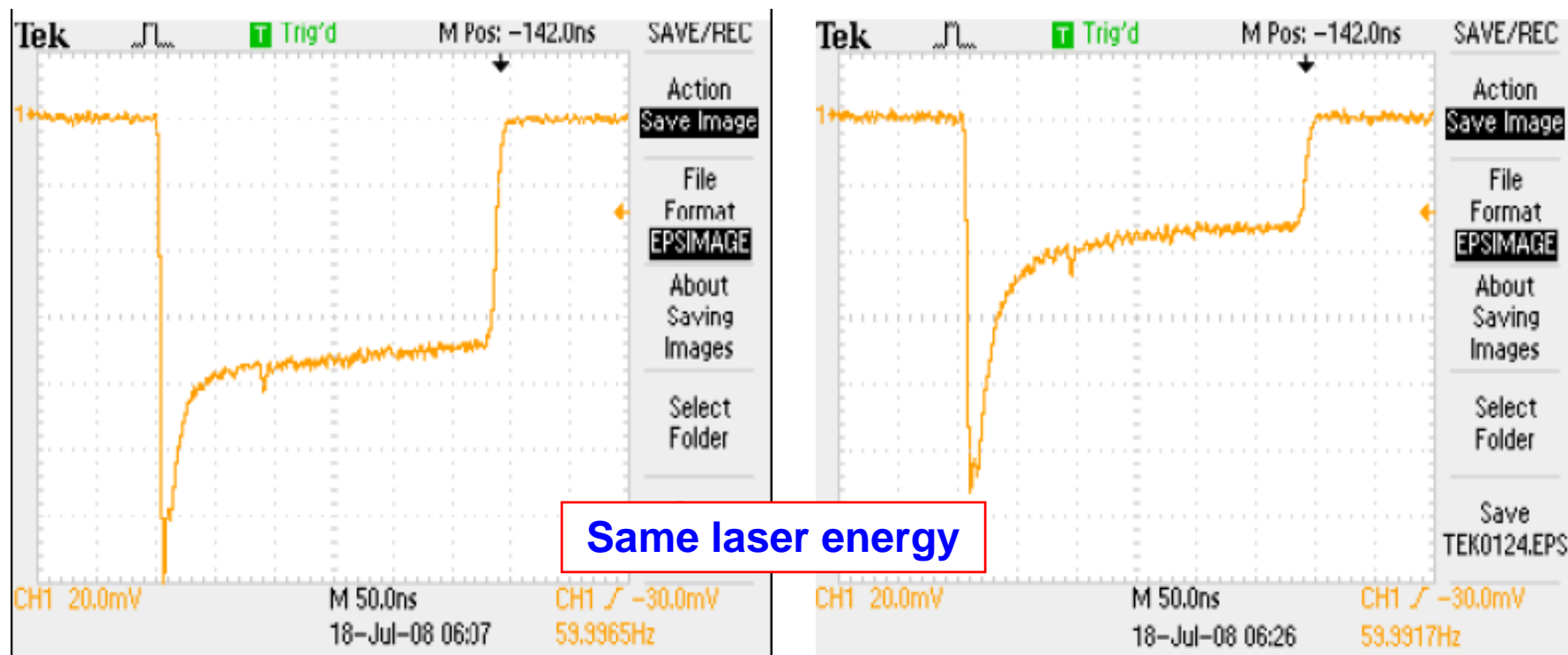


$0.73 \times 10^{10} \text{ e-}$ @ 1x laser energy
10 mm full size



$2.5 \times 10^{10} \text{ e-}$ @ 8x laser energy
10 mm full size

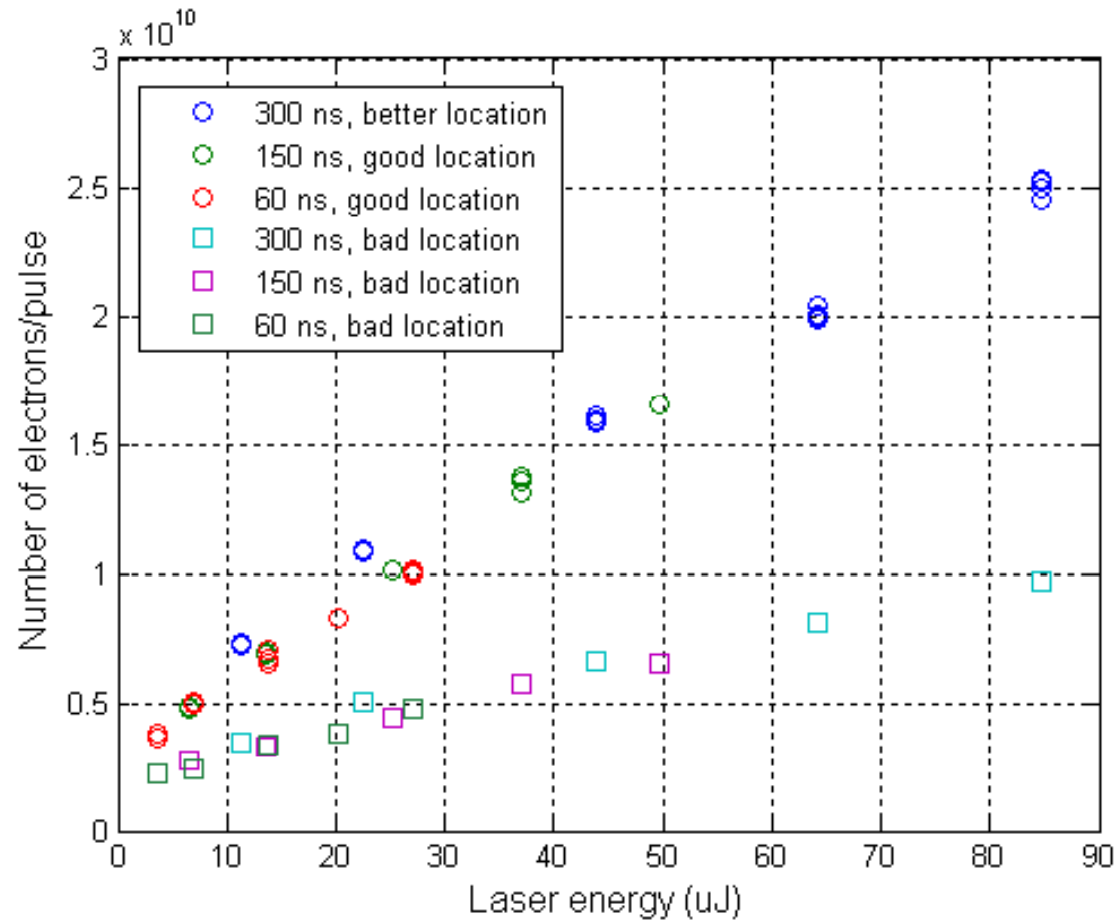
Surface charge: laser location



2.5×10^{10} e- production
10 mm full size @ good location

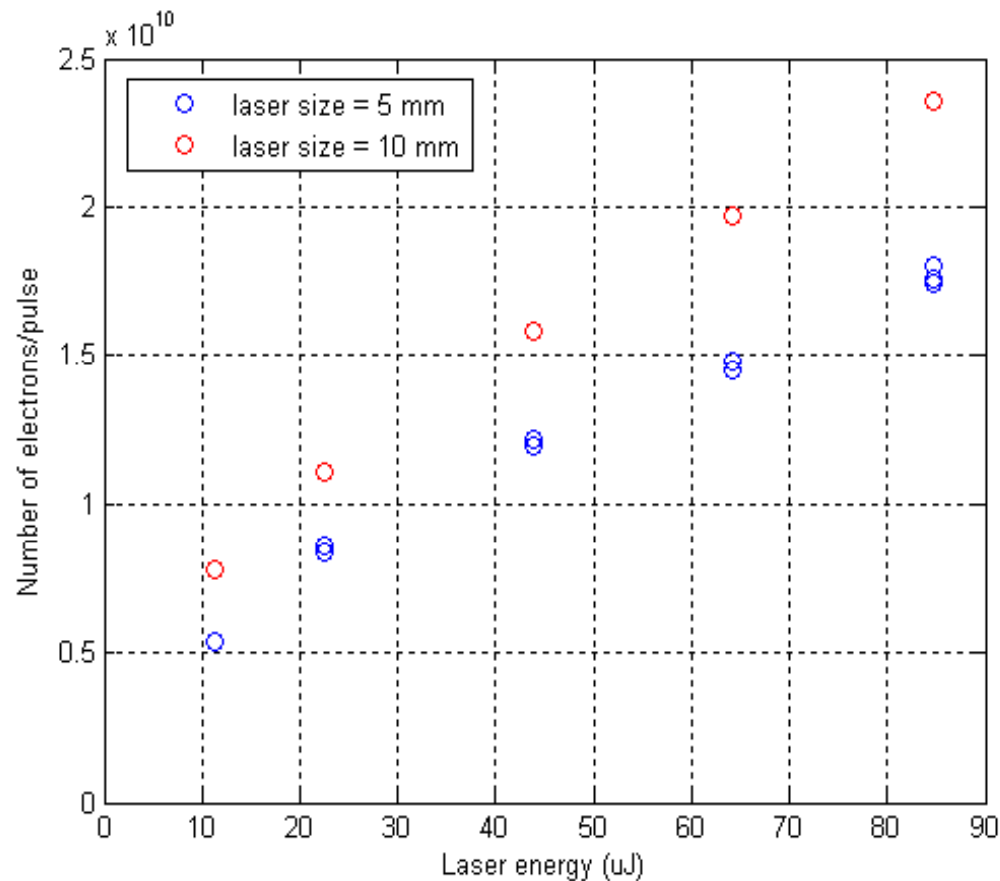
1.4×10^{10} e- production
10 mm full size @ bad location

Charge limit: laser energy



10 mm laser full size

Charge limit: beam size



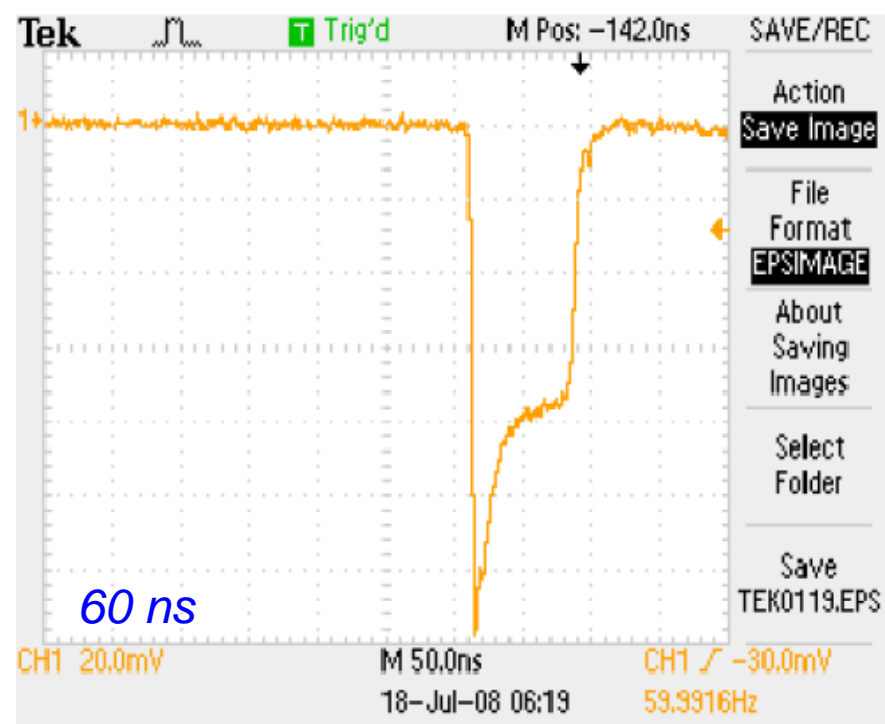
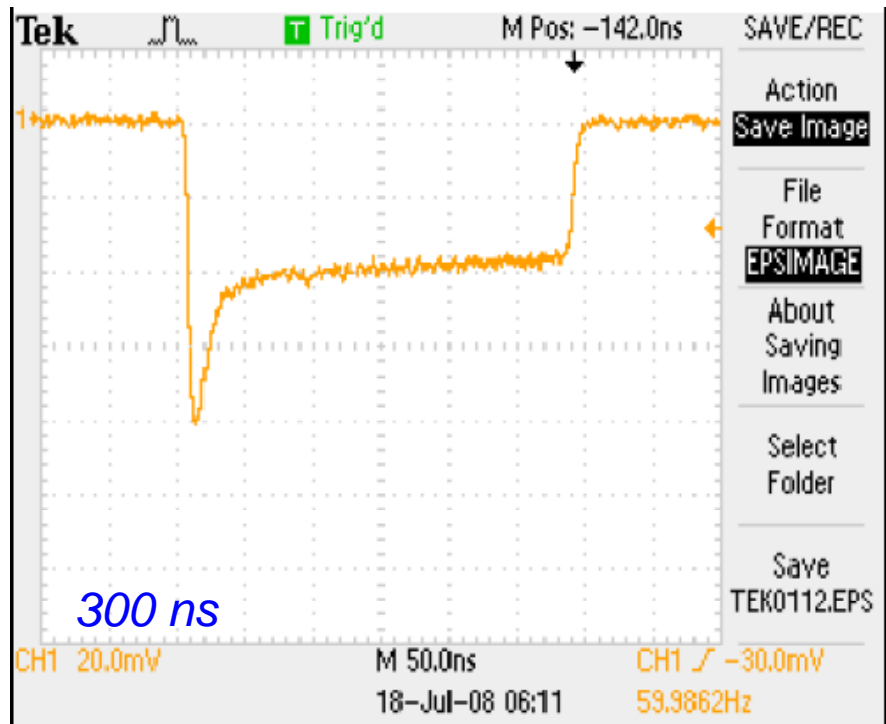
- Space charge (Child's law)

$$J_0 = (2.33 \times 10^{-6}) V^{3/2} / d^2$$

$$J_0 = 10 \text{ A/cm}^2 \text{ @ GTL gun}$$

- Take beam parameters
 $d=5\text{mm}$, $Q=3.75 \text{ nC}$,
 300 ns , $J_0=0.06 \text{ A/cm}^2$
- Space charge negligible
at current conditions;
thus surface charge limit
dominates at smaller size
with $7 \times 10^{18} / \text{cm}^3$ of doping
at the surface layer.

Surface charge: pulse length



*same laser energy
10 mm laser full size*

And what about at 1 ns?

What's the possible indications from the measurements for ILC and CLIC: surface charge & space charge?

	ILC	CLIC
Microbunch	$300\text{ ns} \rightarrow 1\text{ ns}$ Surface charge better Space charge worse	$300\text{ ns} \rightarrow 100\text{ ps}$ Surface charge better Space charge much worse
Macropulse	1 ms (360 ns spacing) Accumulated surface charge may be much worse?	156 ns (0.5 ns spacing) Surface charge may accumulate
Current intensity ($r=1\text{ cm}$)	1.5 A/cm^2 Surface charge and space charge combined; Surface charge may be serious in macropulse?	3.0 A/cm^2 Space charge serious; Surface charge may accumulate in macropulse



Summary and plans

- Measurements for InAlGaAs/AlGaAs cathode at SLAC:
 - **0.2-0.3% QE but can be increased to 1% level after Atomic hydrogen cleaning.**
 - **QE lifetime is very long >400 hrs!**
 - **86% polarization compared with 93% of Russian data**
 - **However, surface charge limit is observed, current intensity 0.06 A/cm^2 @ $7 \times 10^{18} \text{ /cm}^3$ of doping in surface. We need to tune the cathode parameters.**
 - **First observation of polarization dependence on surface charge limit.**



Summary and plans (con't)

- To demonstrate full charge production (surface charge and space charge) for the ILC once its laser ready. The ILC laser expected ready in the early of next year.
- To improve baseline cathode GaAs/GaAsP in the next few yrs with SBIR supports:
 - Study doping level in the structure of GaAs/GaAsP
 - Gradient doping in the active layer
 - Apply both techniques into GaAs/GaAsP
- To study alternate cathodes: tune InAlGaAs/AlGaAs parameters

Doping level in GaAs/GaAsP

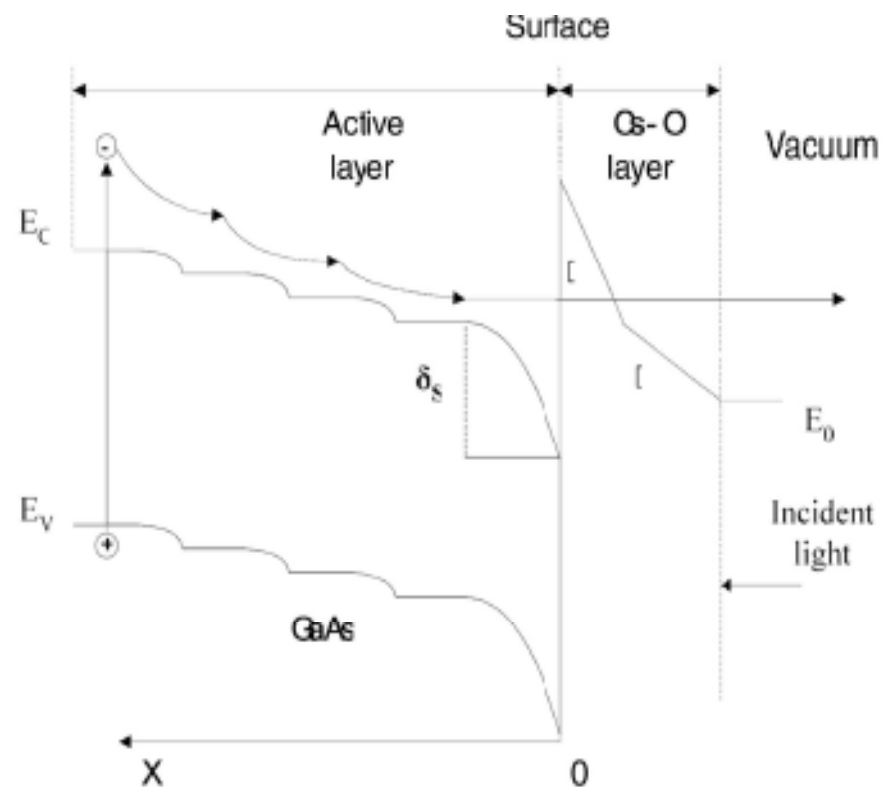
- Doping level at least affects:
 - Smearing band edge and broadening hole spectrum
 - Spin relaxation in transport stage; BAP process
- one of major mechanisms -, exchange interaction between electrons and holes:

$$\frac{1}{\tau_s} = N_h \sigma_{BAP} v$$

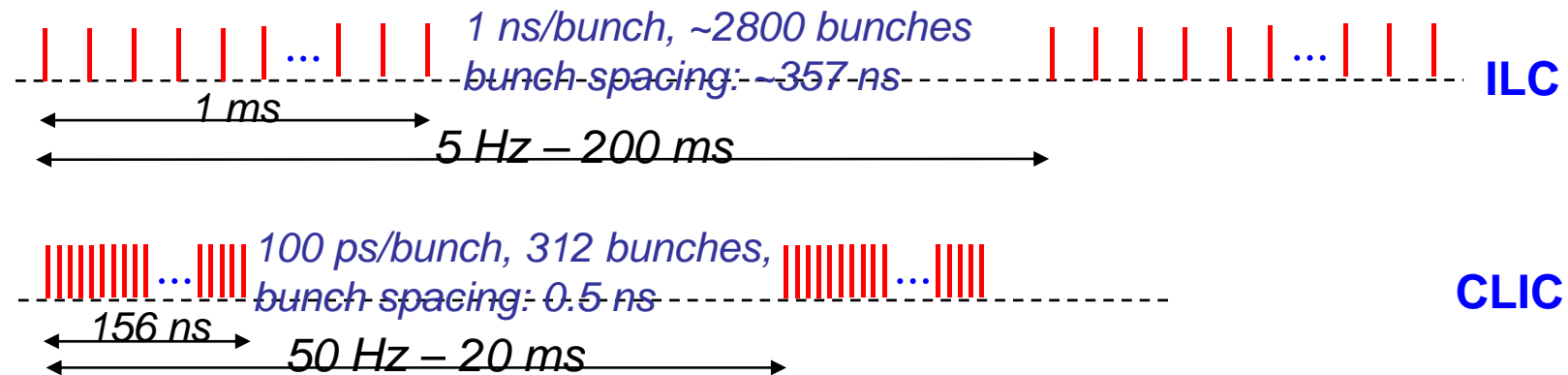
- Spin relaxation in BBR
- Surface charge limit

Gradient doping in the active layer

- Electrons are accelerated when getting through band-bending regions
- High QE expected
- Much interest in gradient doping in the active layer of SL structure.



Summary and plans (con't)



- To demonstrate CLIC-like beam production by using existing 76 MHz ML oscillator (13 ns spacing) or real CLIC laser.
- SLAC's dc-Gun Test Lab with multi-lasers is a worldwide unique diagnostic to characterize polarized photocathodes for both ILC and CLIC: **charge limit, polarization, QE, and QE lifetime.**